

TOSHIBA Diode Silicon Epitaxial Pin Type

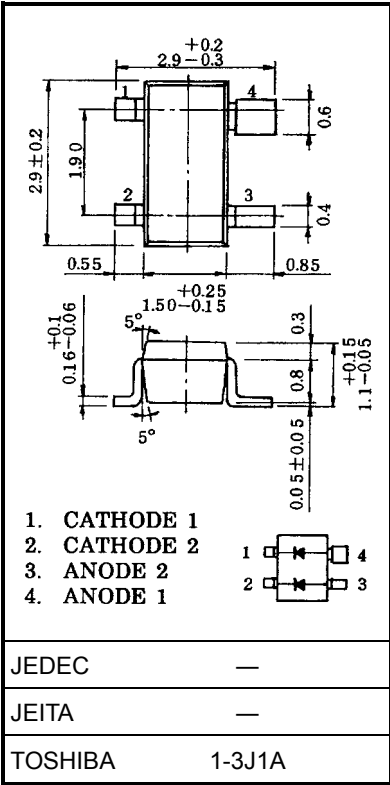
1SV237

VHF~UHF Band RF Attenuator Applications

Unit: mm

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	50	V
Forward current	I_F	50	mA
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C



Electrical Characteristics (Ta = 25°C)

Weight: 0.013 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 10 \mu A$	50	—	—	V
Reverse current	I_R	$V_R = 50 V$	—	—	0.1	μA
Forward voltage	V_F	$I_F = 50 mA$	—	0.95	—	V
Total capacitance	C_T	$V_R = 50 V, f = 1 MHz$	—	0.25	—	pF
Series resistance	r_s	$I_F = 10 mA, f = 100 MHz$	—	3.5	—	Ω

Marking

